

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +70°C	I _D	-6.5 -5.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2	A
Avalanche Current (Note 7) L=0.3mH			I _{AS}	13.2	A
Avalanche Energy (Note 7) L=0.3mH			E _{AS}	26	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.1	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	24	38	mΩ	V _{GS} = -4.5V, I _D = -5A
		—	33	56		V _{GS} = -2.5V, I _D = -4.3A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -2.1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1496	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	130	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	116	—	pF	
Total Gate Charge	Q _g	—	14.4	—	nC	V _{DS} = -10V, V _{GS} = -4.5V I _D = -4.5A
Gate-Source Charge	Q _{gs}	—	2.6	—		
Gate-Drain Charge	Q _{gd}	—	2.7	—		
Turn-On Delay Time	t _{D(ON)}	—	13.7	—	ns	V _{DD} = -10V, V _{GS} = -4.5V, R _g = 6Ω, R _L = 10Ω, I _D = -1A
Turn-On Rise Time	t _r	—	14.0	—		
Turn-Off Delay Time	t _{D(OFF)}	—	79.1	—		
Turn-Off Fall Time	t _f	—	35.5	—		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

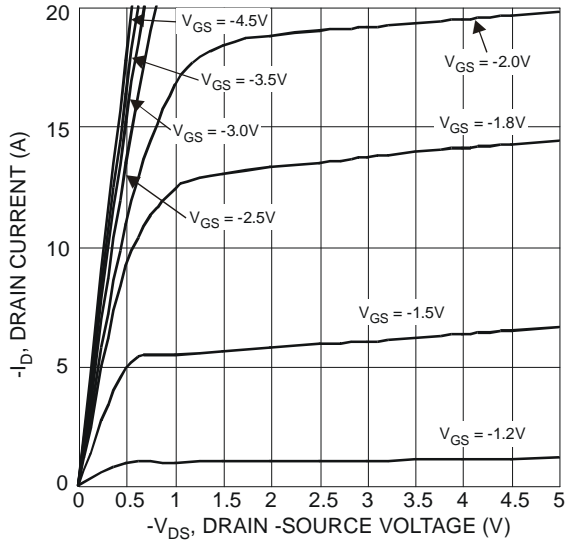


Figure 1 Typical Output Characteristics

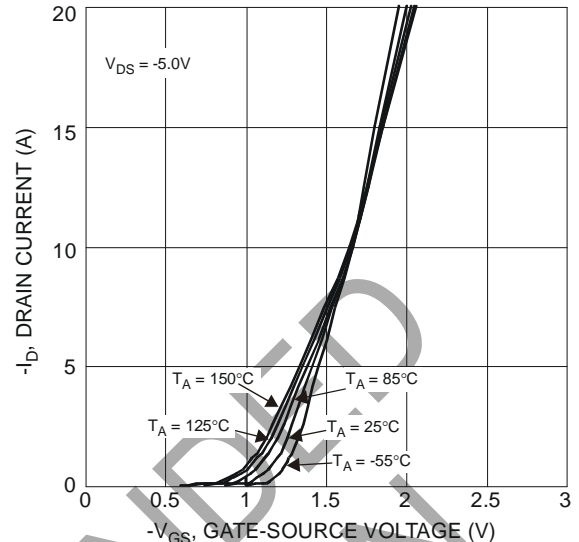


Figure 2 Typical Transfer Characteristics

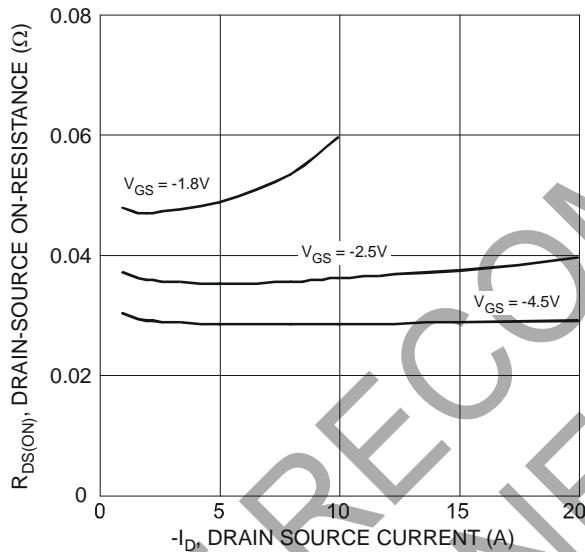


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

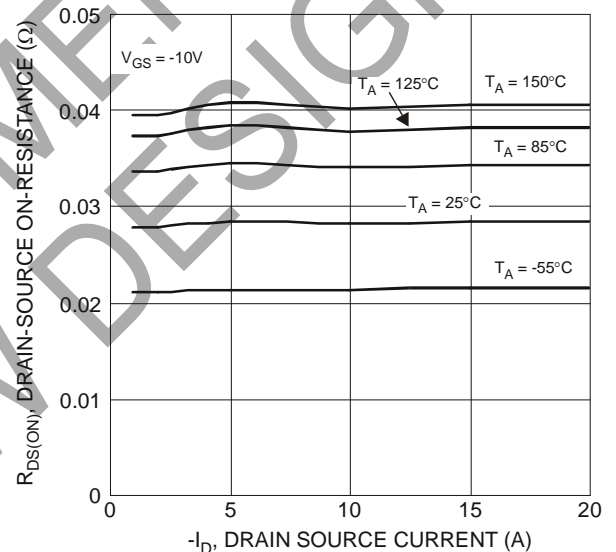


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

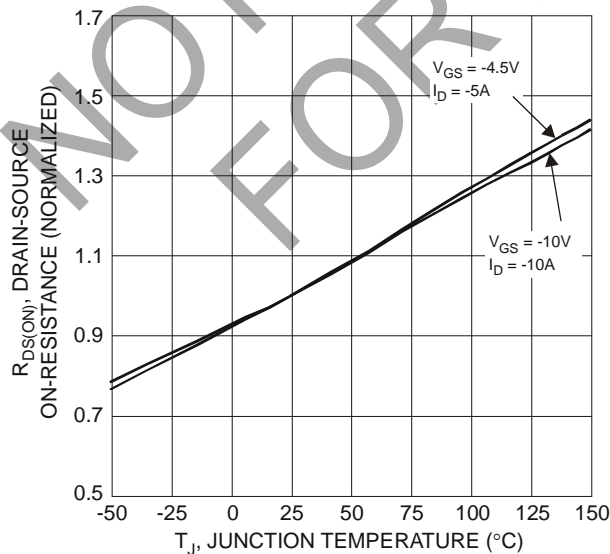


Figure 5 On-Resistance Variation with Temperature

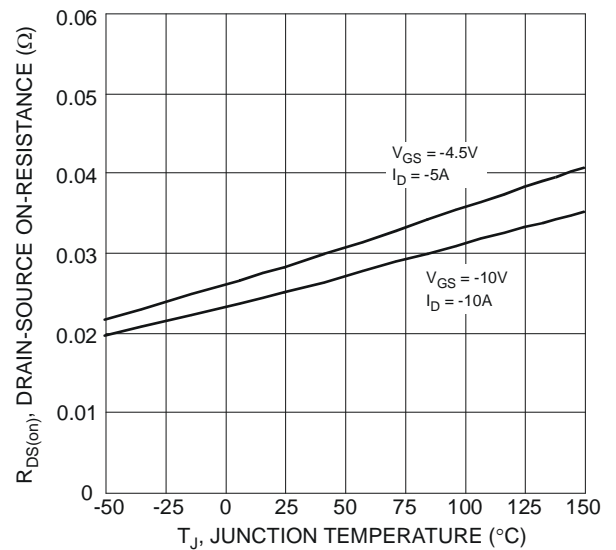


Figure 6 On-Resistance Variation with Temperature

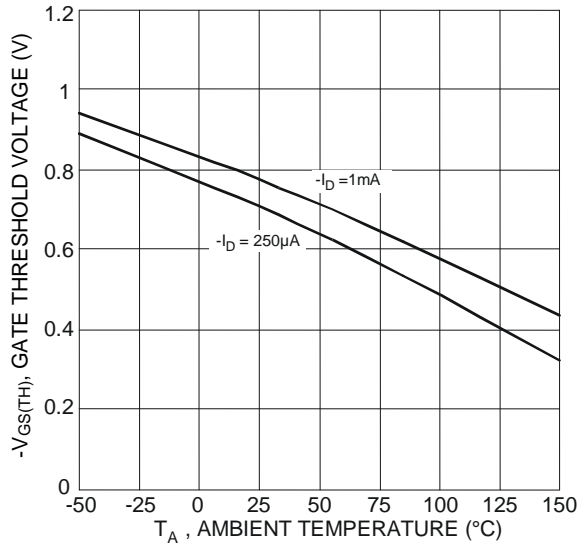


Figure 7 Gate Threshold Variation vs. Ambient Temperature

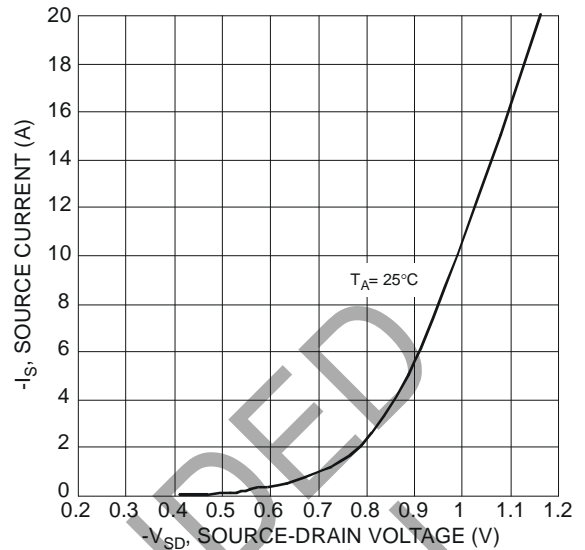


Figure 8 Diode Forward Voltage vs. Current

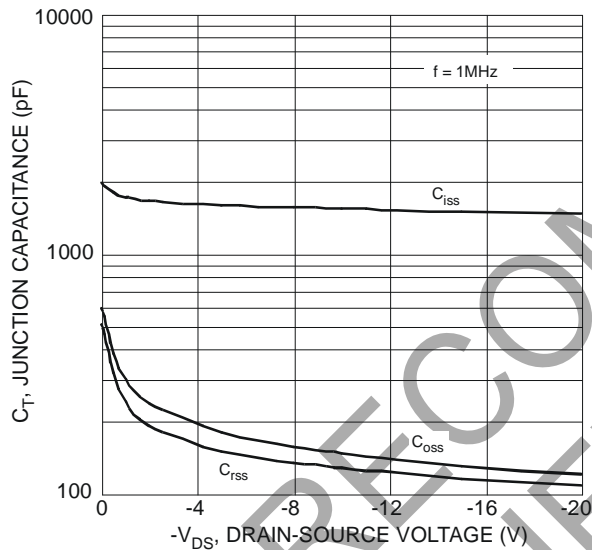


Figure 9 Typical Junction Capacitance

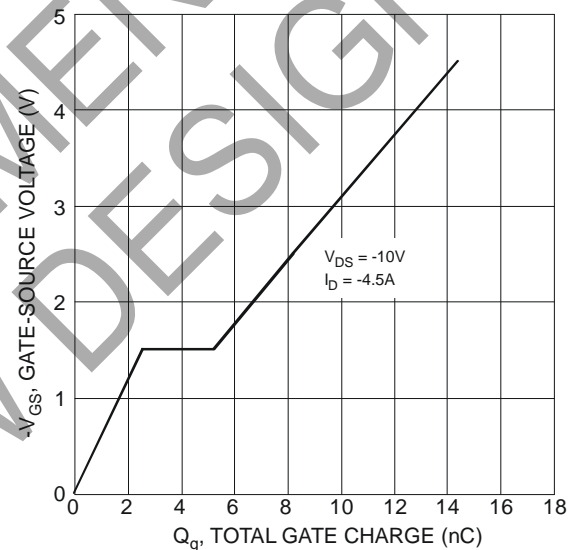


Figure 10 Gate-Charge Characteristics

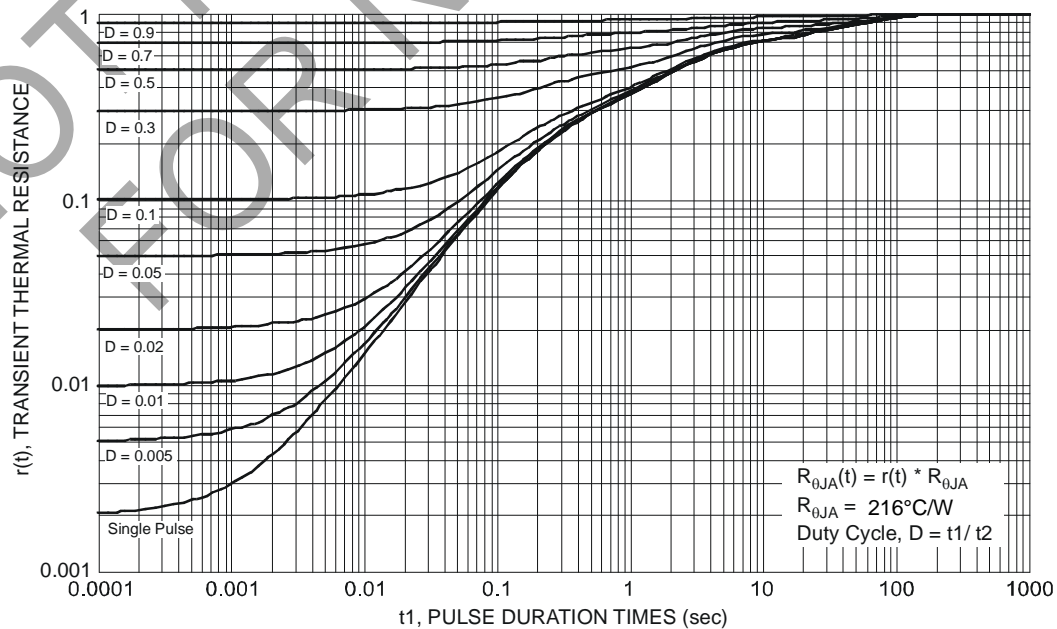


Figure 11 Transient Thermal Resistance

$$R_{\theta JA}(t) = r(t) * R_{\theta JA}$$

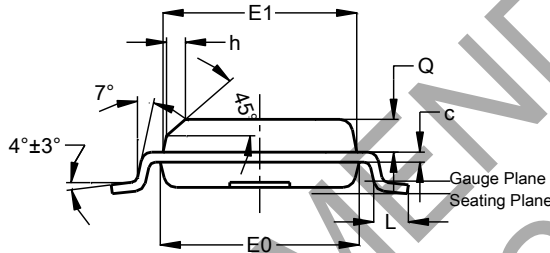
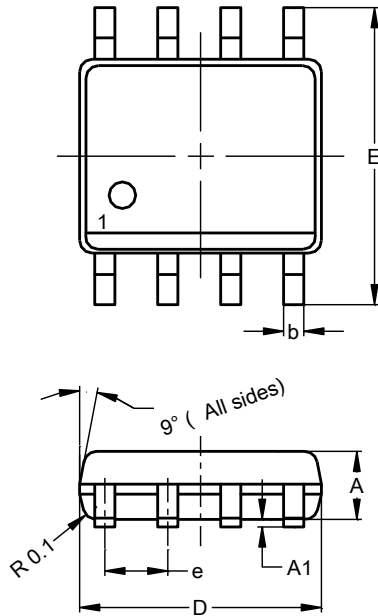
$$R_{\theta JA} = 216^{\circ}\text{C/W}$$

$$\text{Duty Cycle, } D = t_1 / t_2$$

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

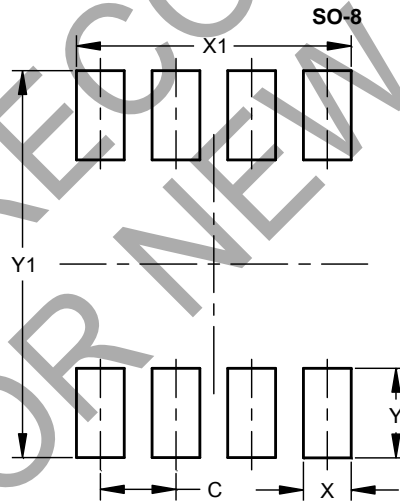
SO-8



SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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